

1. General Description

The 74HC2G14 and 74HCT2G14 are dual inverters with Schmitt-trigger inputs. Inputs are overvoltage tolerant. This feature allows the use of these devices as translators in mixed voltage environments.

The AHC device has CMOS input switching levels and supply voltage range 2 V to 5.5 V.

The AHCT device has TTL input switching levels and supply voltage range 4.5 V to 5.5 V.

2. Features and Benefits

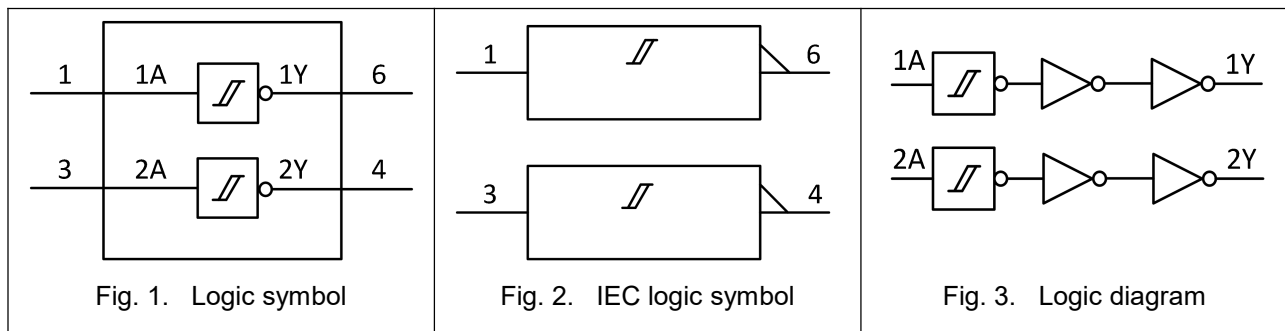
- Wide supply voltage range from 2.0 V to 5.5 V
- Overvoltage tolerant inputs to 5.5 V
- High noise immunity
- CMOS low power dissipation
- Latch-up performance exceeds 200 mA
- Symmetrical output impedance
- Balanced propagation delays
- Input levels:
 - For 74HC2G14: CMOS level
 - For 74HCT2G14: TTL level
- ESD protection:
 - HBM ANSI/ESDA/JEDEC JS-001 Class 3A exceeds 7000 V
 - CDM ANSI/ESDA/JEDEC JS-002 Class C3 exceeds 2000 V
- Multiple package options

3. Ordering Information

Table 1. Ordering information

Type number	Package		
	Name	Description	Quantity
74HC2G14GV	SOT23-6L	SOT23 package, 6 pins 2.92 mm × 1.6 mm; 1.25 mm (Max) height	3000
74HCT2G14GV			
74HC2G14GW	SOT363	SOT363 package, 6 pins 2.1 mm × 1.25 mm; 1.1 mm (Max) height	3000
74HCT2G14GW			
74HC2G14DRL	SOT563	SOT563 package, 6 pins 1.6 mm × 1.2 mm; 0.6 mm (Max) height	3000
74HCT2G14DRL			

4. Function Diagram



5. Pinning Information

5.1. Pinning

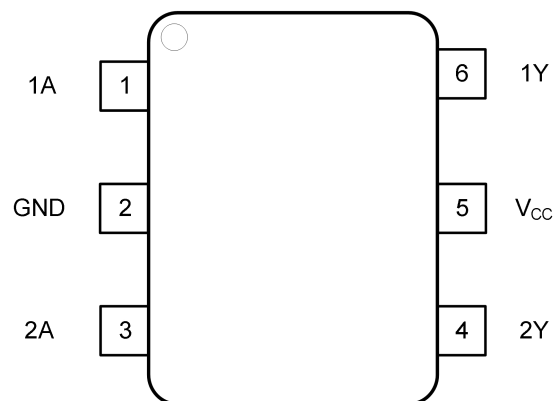


Fig. 4. Top view pin configuration SOT23-5L, SOT353 and SOT553

5.2. Pin description

Table 2. Pin description

Symbol	Pin	Description
1A	1	Data input
GND	2	Ground (0V)
2A	3	Data input
2Y	4	Data output
V _{CC}	5	Supply voltage
1Y	6	Data output

6. Functional Description

Table 3. Function table

H = HIGH voltage level; L = LOW voltage level.

Input	Output
A	Y
L	H
H	L

7. Absolute Maximum Ratings

Stresses exceeding the absolute maximum ratings may damage the device. The device may not function or be operable above the recommended operating conditions and stressing the parts to these levels is not recommended. In addition, extended exposure to stresses above the recommended operating conditions may affect device reliability. The absolute maximum ratings are stress ratings only.

Table 4. Absolute Maximum Ratings

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND.

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CC}	supply voltage		-0.5	7.0	V
V_I	input voltage		-0.5	7.0	V
I_{IK}	input clamping current	$V_I < -0.5\text{ V}$	-20		mA
I_{OK}	output clamping current	$V_O < -0.5\text{ V}$ or $V_O > V_{CC} + 0.5\text{ V}$ [1]		± 20	mA
I_O	output current	$-0.5\text{ V} < V_O < V_{CC} + 0.5\text{ V}$		± 25	mA
I_{CC}	supply current			75	mA
I_{GND}	ground current		-75		mA
P_{tot}	total power dissipation	$T_{amb} = -40\text{ °C to } +125\text{ °C}$		250	mW
T_{stg}	storage temperature		-65	150	°C

[1] The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

8. Recommended Operating Conditions

The Recommended Operating Conditions table defines the conditions for actual device operation. Recommended operating conditions are specified to ensure optimal performance to the datasheet specifications. EnergyMath does not recommend exceeding them or designing to Absolute Maximum Ratings.

Table 5. Recommended Operating Conditions

Symbol	Parameter	Conditions	74HC2G14			74HCT2G14			Unit
			Min	Typ	Max	Min	Typ	Max	
V_{CC}	supply voltage		2.0	5.0	5.5	4.5	5.0	5.5	V
V_I	input voltage		0		5.5	0		5.5	V
V_O	output voltage		0		V_{CC}	0		V_{CC}	V
T_{amb}	ambient temperature		-40	25	125	-40	25	125	°C

9.Static Characteristics

Table 6. Static characteristics

At recommended operating conditions. Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	-40 °C to +85 °C			-40 °C to +125 °C		Unit
			Min	Typ[1]	Max	Min	Max	
74HC2G14								
V _{OH}	HIGH-level output voltage	V _I = V _{T+} or V _{T-}						
		I _O = -50 μA; V _{CC} = 2.0 V	1.9	2.0		1.9		V
		I _O = -50 μA; V _{CC} = 3.0 V	2.9	3.0		2.9		V
		I _O = -50 μA; V _{CC} = 4.5 V	4.4	4.5		4.4		V
		I _O = -4.0 mA; V _{CC} = 3.0 V	2.48	2.93		2.40		V
		I _O = -8.0 mA; V _{CC} = 4.5 V	3.80	4.39		3.70		V
V _{OL}	LOW-level output voltage	V _I = V _{T+} or V _{T-}						
		I _O = 50 μA; V _{CC} = 2.0 V		0	0.1		0.1	V
		I _O = 50 μA; V _{CC} = 3.0 V		0	0.1		0.1	V
		I _O = 50 μA; V _{CC} = 4.5 V		0	0.1		0.1	V
		I _O = 4.0 mA; V _{CC} = 3.0 V		0.05	0.44		0.55	V
		I _O = 8.0 mA; V _{CC} = 4.5 V		0.07	0.44		0.55	V
I _I	input leakage current	V _I = 5.5 V or GND ; V _{CC} = 0 V to 5.5 V		±0.01	±1.0		±2.0	μA
I _{CC}	supply current	V _I = V _{CC} or GND ; I _O = 0 A ; V _{CC} = 5.5 V		0.01	10		40	μA
C _I	input capacitance			3.5				pF

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Dual inverting Schmitt trigger

Symbol	Parameter	Conditions	-40 °C to +85 °C			-40 °C to +125 °C		Unit
			Min	Typ[1]	Max	Min	Max	
74HCT2G14								
V _{OH}	HIGH-level output voltage	V _I = V _{T+} or V _{T-} ; V _{CC} = 4.5 V						
		I _O = -50 µA;	4.4	4.5		4.4		V
		I _O = -8.0 mA;	3.80	4.39		3.70		V
V _{OL}	LOW-level output voltage	V _I = V _{T+} or V _{T-} ; V _{CC} = 4.5 V						
		I _O = 50 µA;		0	0.1		0.1	V
		I _O = 8.0 mA;		0.07	0.44		0.55	V
I _I	input leakage current	V _I = 5.5 V or GND ; V _{CC} = 0 V to 5.5 V		±0.01	±1.0		±2.0	µA
I _{CC}	supply current	V _I = V _{CC} or GND ; I _O = 0 A ; V _{CC} = 5.5 V		0.01	10		40	µA
ΔI _{CC}	additional supply current	per input pin ; V _I = 3.4 V; other inputs at V _{CC} or GND; I _O = 0 A; V _{CC} = 5.5 V		0.23	1.35		1.35	mA
C _I	input capacitance			3.5				pF

[1] All typical values are measured at $T_{amb} = 25^\circ\text{C}$.

10. Dynamic Characteristics

Table 7. Dynamic characteristics

Voltages are referenced to GND (ground = 0 V); for test circuit see Fig. 6.

Symbol	Parameter	Conditions	-40 °C to +85 °C			-40 °C to +125 °C		Unit
			Min	Typ[1]	Max	Min	Max	
74HC2G14								
t _{pd}	propagation delay	nA to nY; see Fig. 5 [2]						
		V _{CC} = 3.0 V to 3.6 V, C _L = 15 pF	1.5	6.1	12	1.5	13	ns
		V _{CC} = 4.5 V to 5.5 V, C _L = 15 pF	1.5	3.9	8.5	1.5	9.0	ns
C _{PD}	power dissipation capacitance	C _L = 15 pF ; f = 1MHz ; V _I = GND to V _{CC} ; [3]		20				pF
74HCT2G14								
t _{pd}	propagation delay	nA to nY; see Fig. 5 [2]						
		V _{CC} = 4.5 V to 5.5 V, C _L = 15 pF	1.5	5.0	10.0	1.5	10.5	ns
C _{PD}	power dissipation capacitance	C _L = 15 pF ; f = 1MHz ; V _I = GND to V _{CC} ; [3]		21				pF

[1] Typical values are measured at $T_{amb} = 25 \text{ °C}$ and $V_{CC} = 3.3 \text{ V}$ and 5.0 V respectively.

[2] t_{pd} is the same as t_{PLH} and t_{PHL} .

[3] C_{PD} is used to determine the dynamic power dissipation (P_D in μW).

$P_D = C_{PD} \times V_{CC}^2 \times f_i \times N + \Sigma(C_L \times V_{CC}^2 \times f_o)$ where:

f_i = input frequency in MHz;

f_o = output frequency in MHz;

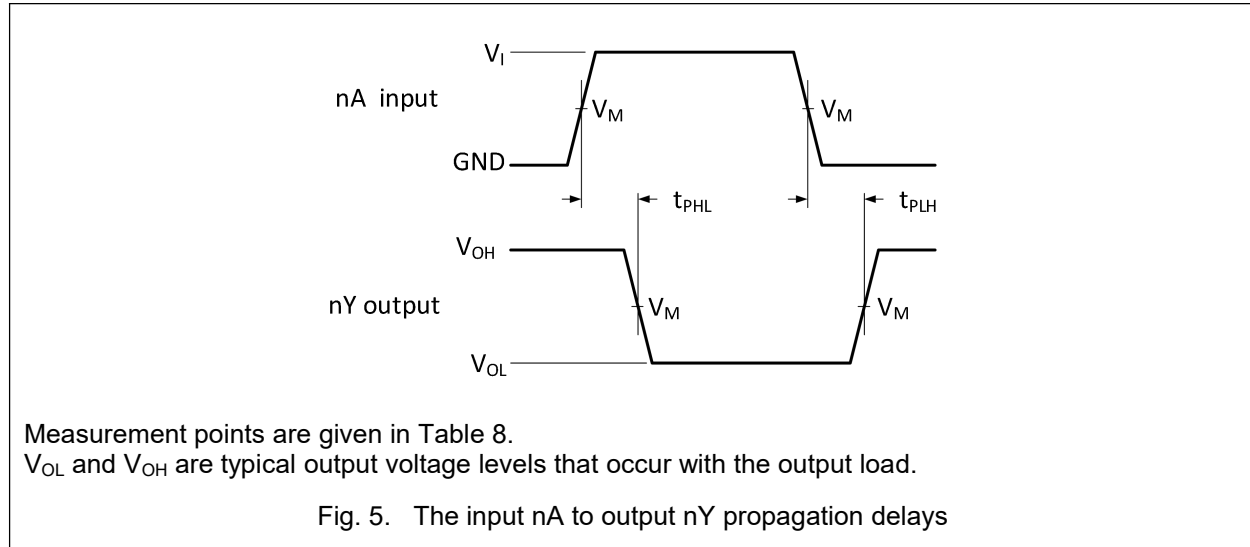
C_L = output load capacitance in pF;

V_{CC} = supply voltage in V;

N = number of inputs switching;

$\Sigma(C_L \times V_{CC}^2 \times f_o)$ = sum of outputs.

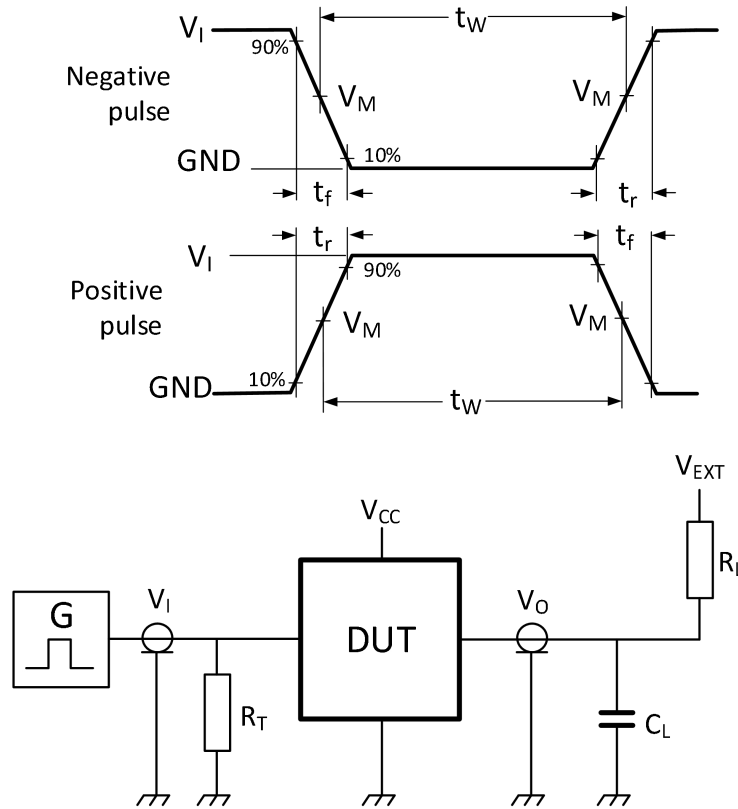
10.1. Waveforms and test circuit


Table 8. Measurement points

Type	Input		Output
	V_I	V_M	V_M
74HC2G14	GND to V_{CC}	$0.5 \times V_{CC}$	$0.5 \times V_{CC}$
74HCT2G14	GND to 3.0 V	1.5 V	$0.5 \times V_{CC}$

74HC2G14; 74HCT2G14

Dual inverting Schmitt trigger



Test data is given in Table 9.

Definitions for test circuit:

R_L = Load resistance.

C_L = Load capacitance including jig and probe capacitance.

R_T = Termination resistance should be equal to the output impedance Z_o of the pulse generator.

V_{EXT} = External voltage for measuring switching times.

Fig. 6. Test circuit for measuring switching times

Table 9. Test data

Type	Input		Load		V_{EXT}
	V_I	$t_r = t_f$	C_L	R_L	t_{PD}
74HC2G14	GND to V_{CC}	≤ 2.5 ns	15 pF	500 Ω	open
74HCT2G14	GND to 3.0 V	≤ 2.5 ns	15 pF	500 Ω	open

11. Transfer Characteristics

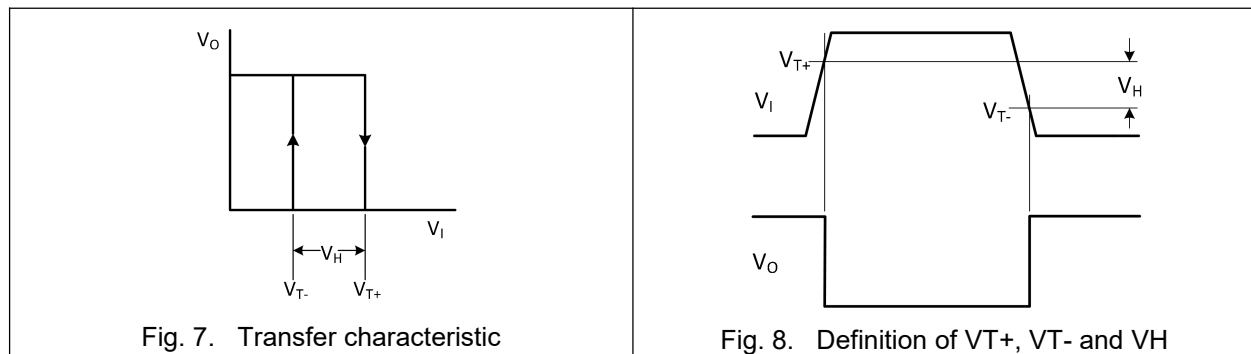
Table 10. Transfer characteristics

At recommended operating conditions. Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	-40 °C to +85 °C			-40 °C to +125 °C		Unit
			Min	Typ[1]	Max	Min	Max	
74HC2G14								
V _{T+}	positive-going threshold voltage	V _{CC} = 3.0 V			2.2		2.2	V
		V _{CC} = 4.5 V			3.15		3.15	V
		V _{CC} = 5.5 V			3.85		3.85	V
V _{T-}	negative-going threshold voltage	V _{CC} = 3.0 V	0.85			0.85		V
		V _{CC} = 4.5 V	1.35			1.35		V
		V _{CC} = 5.5 V	1.65			1.65		V
V _H	hysteresis voltage	V _{CC} = 3.0 V	0.3		1.2	0.25	1.2	V
		V _{CC} = 4.5 V	0.4		1.4	0.35	1.4	V
		V _{CC} = 5.5 V	0.5		1.6	0.45	1.6	V
74HCT2G14								
V _{T+}	positive-going threshold voltage	V _{CC} = 4.5 V			2.0		2.0	V
		V _{CC} = 5.5 V			2.0		2.0	V
V _{T-}	negative-going threshold voltage	V _{CC} = 4.5 V	0.5			0.5		V
		V _{CC} = 5.5 V	0.6			0.6		V
V _H	hysteresis voltage	V _{CC} = 4.5 V	0.4		1.4	0.35	1.4	V
		V _{CC} = 5.5 V	0.4		1.6	0.35	1.6	V

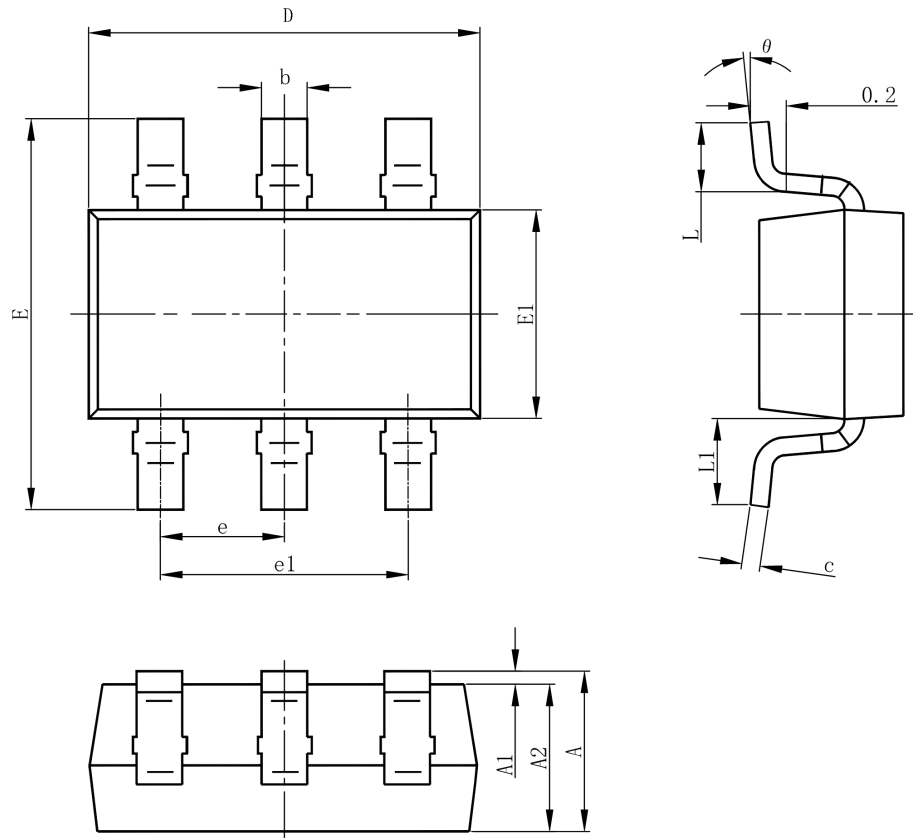
[1] Typical values are measured at $T_{amb} = 25 \text{ °C}$.

11.1. Waveforms transfer characteristics



12. Package Outline

SOT23-6L

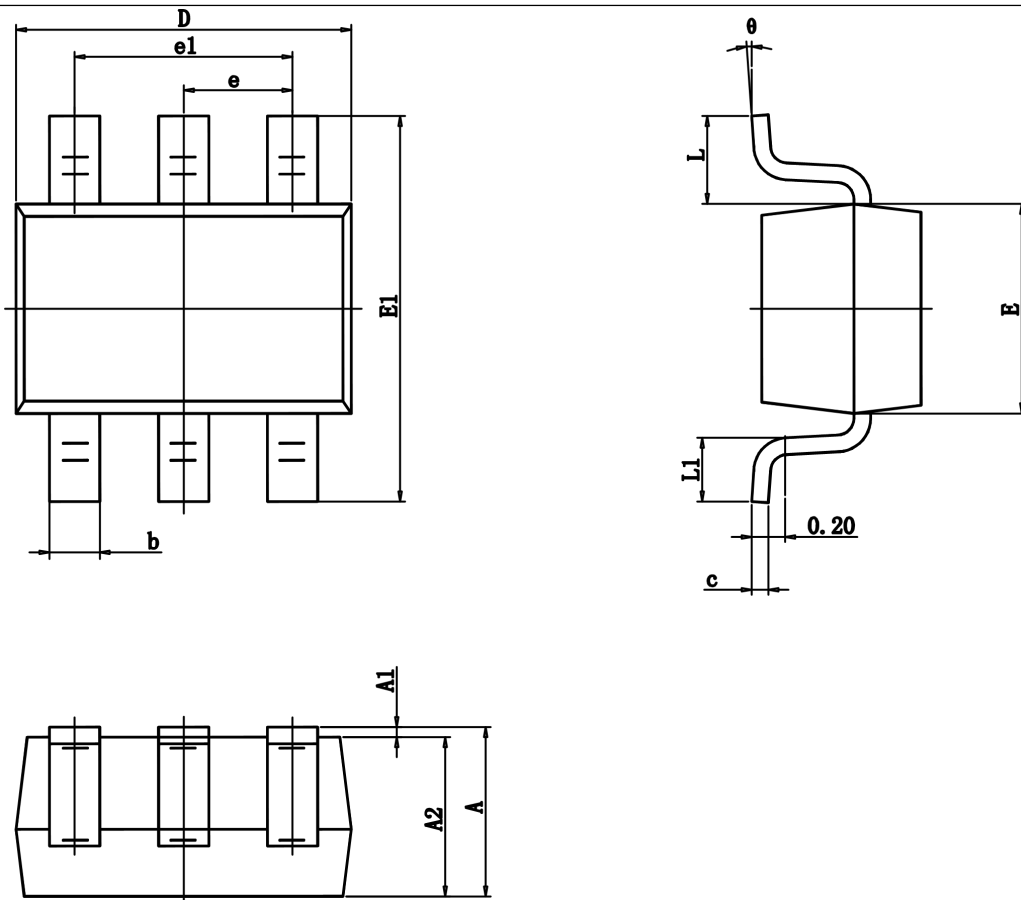


Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	1.050	1.250	0.041	0.049
A1	0.000	0.100	0.000	0.004
A2	1.050	1.150	0.041	0.045
b	0.300	0.500	0.012	0.020
c	0.100	0.200	0.004	0.008
D	2.820	3.020	0.111	0.119
E1	1.500	1.700	0.059	0.067
E	2.650	2.950	0.104	0.116
e	0.950(BSC)		0.037(BSC)	
e1	1.800	2.000	0.071	0.079
L	0.300	0.600	0.012	0.024
L1	0.600REF.		0.024REF.	
θ	0°	8°	0°	8°

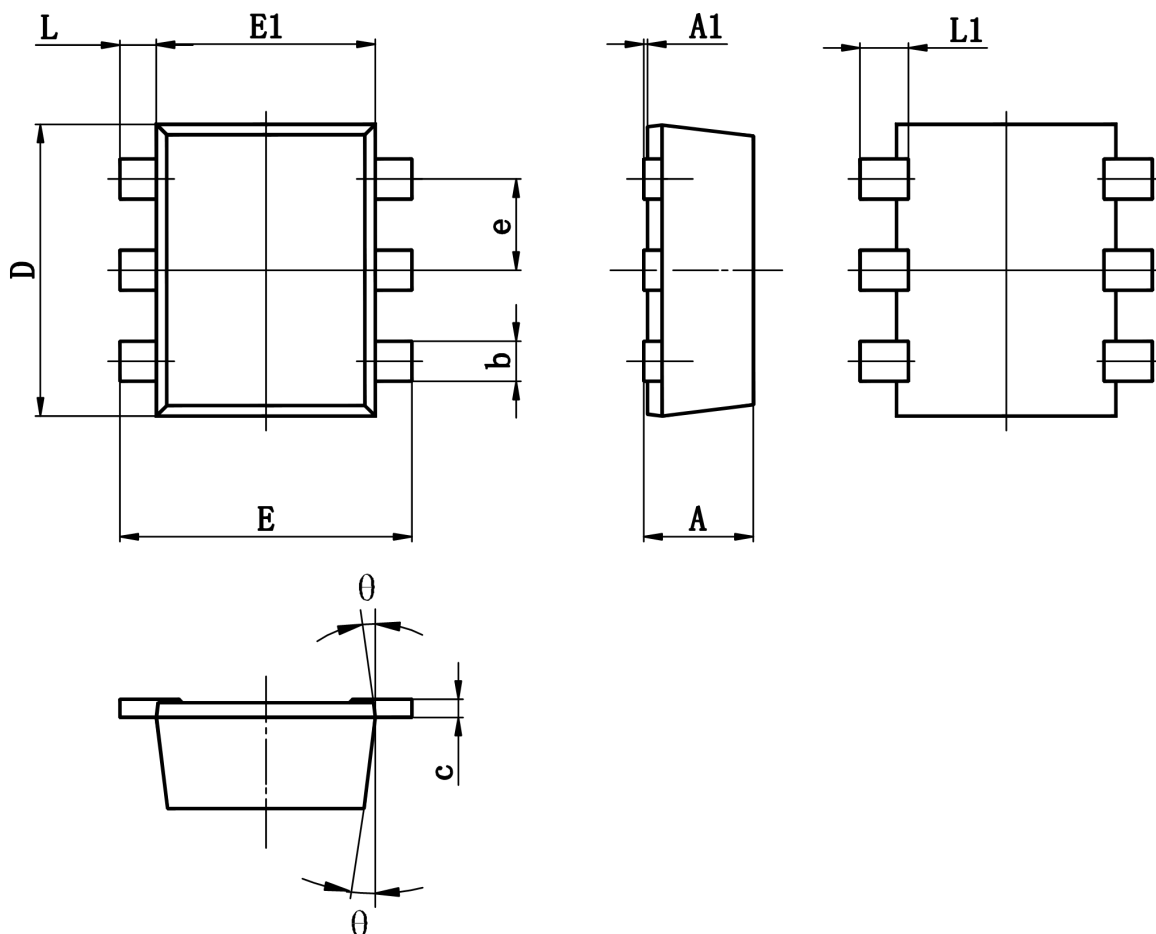
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Dual inverting Schmitt trigger

SOT363



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.900	1.100	0.035	0.043
A1	0.000	0.100	0.000	0.004
A2	0.900	1.000	0.035	0.039
b	0.150	0.350	0.006	0.014
c	0.110	0.175	0.004	0.007
D	2.000	2.200	0.079	0.087
E	1.150	1.350	0.045	0.053
E1	2.150	2.450	0.085	0.096
e	0.650 TYP.		0.026 TYP.	
e1	1.200	1.400	0.047	0.055
L	0.525 REF.		0.021 REF.	
L1	0.260	0.460	0.010	0.018
θ	0°	8°	0°	8°

SOT563


Symbol	Dimensions In Millimeters		Dimensions in inches	
	Min.	Max.	Min.	Max.
A	0.525	0.600	0.021	0.024
A1	0.000	0.050	0.000	0.002
e	0.450	0.550	0.018	0.022
c	0.090	0.160	0.004	0.006
D	1.500	1.700	0.059	0.067
b	0.170	0.270	0.007	0.011
E1	1.100	1.300	0.043	0.051
E	1.500	1.700	0.059	0.067
L	0.100	0.300	0.004	0.012
L1	0.200	0.400	0.008	0.016
θ	7° ^{REF.}		7° ^{REF.}	

13. Abbreviations

Table 10. Abbreviations

Acronym	Description
CMOS	Complementary Metal-Oxide Semiconductor
DUT	Device Under Test
ESD	ElectroStatic Discharge
HBM	Human Body Model
CDM	Charged Device Model
TTL	Transistor-Transistor Logic

14. Revision History

Table 11. Revision history

Document ID	Release Date	Data sheet status	Change notice	Supersedes
74HC_HCT2G14 Rev. 1.0	Aug 08, 2024	Product datasheet		